

Single N-channel MOSFET

ELM544634A-N

■ General description

ELM544634A-N uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate resistance.

■ Features

- $V_{ds}=30V$
- $I_d=18A$
- $R_{ds(on)} = 5.8m\Omega$ ($V_{gs}=10V$)
- $R_{ds(on)} = 7.2m\Omega$ ($V_{gs}=4.5V$)

■ Maximum absolute ratings

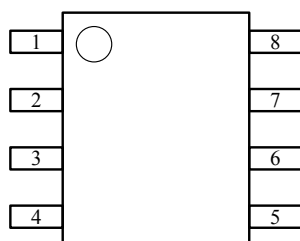
Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{ds}	30	V
Gate-source voltage	V_{gs}	± 20	V
Continuous drain current($T_j=150^\circ C$)	I_d	$T_a=25^\circ C$	18
		$T_a=70^\circ C$	15
Pulsed drain current	I_{dm}	50	A
Power dissipation	P_d	$T_a=25^\circ C$	2.8
		$T_a=70^\circ C$	1.8
Operating junction and storage temperature range	T_j, T_{stg}	-55 to 150	$^\circ C$

■ Thermal characteristics

Parameter	Symbol	Typ.	Max.	Unit
Maximum junction-to-ambient	$R_{\theta ja}$		62.5	$^\circ C/W$

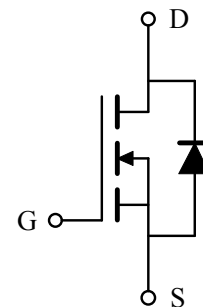
■ Pin configuration

SOP-8(TOP VIEW)



Pin No.	Pin name
1	SOURCE
2	SOURCE
3	SOURCE
4	GATE
5	DRAIN
6	DRAIN
7	DRAIN
8	DRAIN

■ Circuit



Single N-channel MOSFET

ELM544634A-N

■ Electrical characteristics

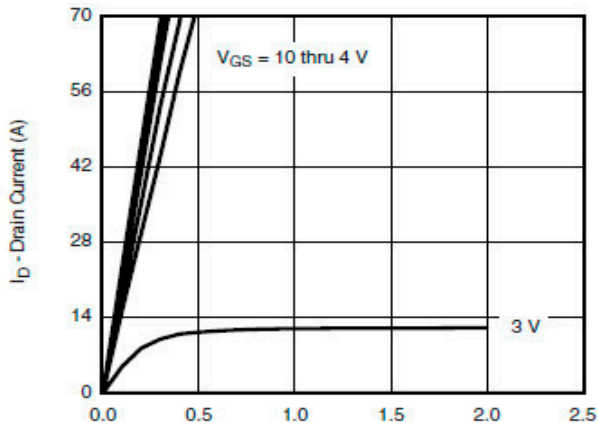
Ta=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	BVdss	Id=250μA, Vgs=0V	30			V
Zero gate voltage drain current	Idss	Vds=24V, Vgs=0V			1	μA
		Vds=24V, Vgs=0V, Tj=85°C			10	
Gate-body leakage current	Igss	Vds=0V, Vgs=±20V			±100	nA
Gate threshold voltage	Vgs(th)	Vds=Vgs, Id=250μA	1.0		2.0	V
On state drain current	Id(on)	Vgs=10V, Vds=5V	15			A
Static drain-source on-resistance	Rds(on)	Vgs=10V, Id=18A		4.8	5.8	mΩ
		Vgs=4.5V, Id=15A		6.0	7.2	
Forward transconductance	Gfs	Vds=15V, Id=10A		24		S
Diode forward voltage	Vsd	Is=10A, Vgs=0V		0.8	1.3	V
Max. body-diode continuous current	Is				3.8	A
DYNAMIC PARAMETERS						
Input capacitance	Ciss	Vgs=0V, Vds=15V, f=1MHz		2800		pF
Output capacitance	Coss			480		pF
Reverse transfer capacitance	Crss			300		pF
SWITCHING PARAMETERS						
Total gate charge	Qg	Vds=15V, Vgs=4.5V Id=10A		22	42	nC
Gate-source charge	Qgs			8		nC
Gate-drain charge	Qgd			7		nC
Turn-on delay time	td(on)	Vgs=10V, Vds=15V RL=1.5Ω, Id=10A Rgen=1.0Ω		15	30	ns
Turn-on rise time	tr			12	20	ns
Turn-off delay time	td(off)			30	50	ns
Turn-off fall time	tf			10	20	ns

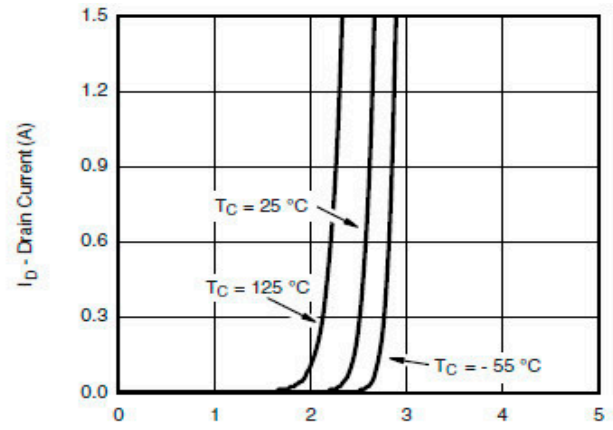
Single N-channel MOSFET

ELM544634A-N

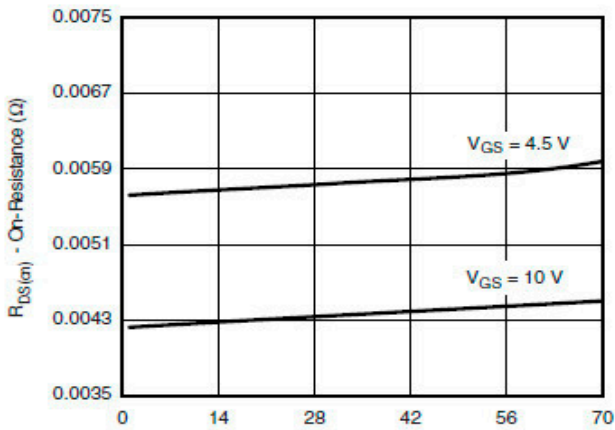
■ Typical electrical and thermal characteristics



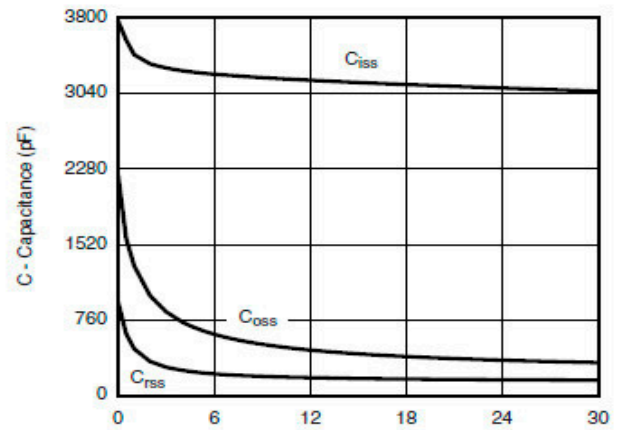
Output Characteristics



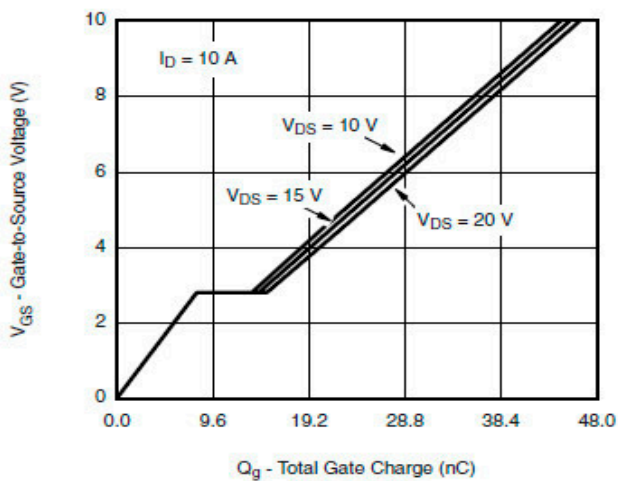
Transfer Characteristics



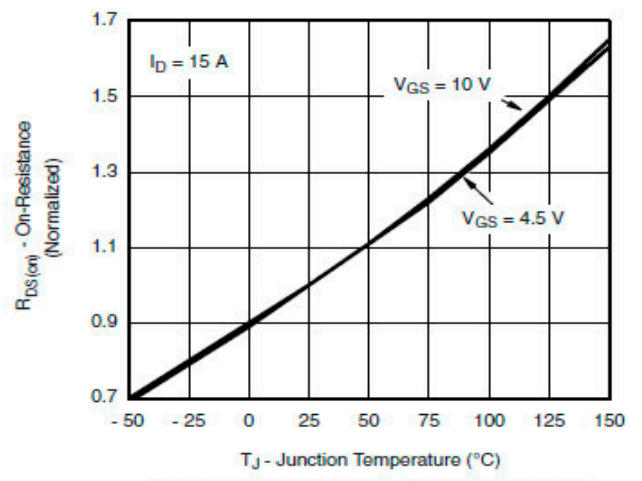
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



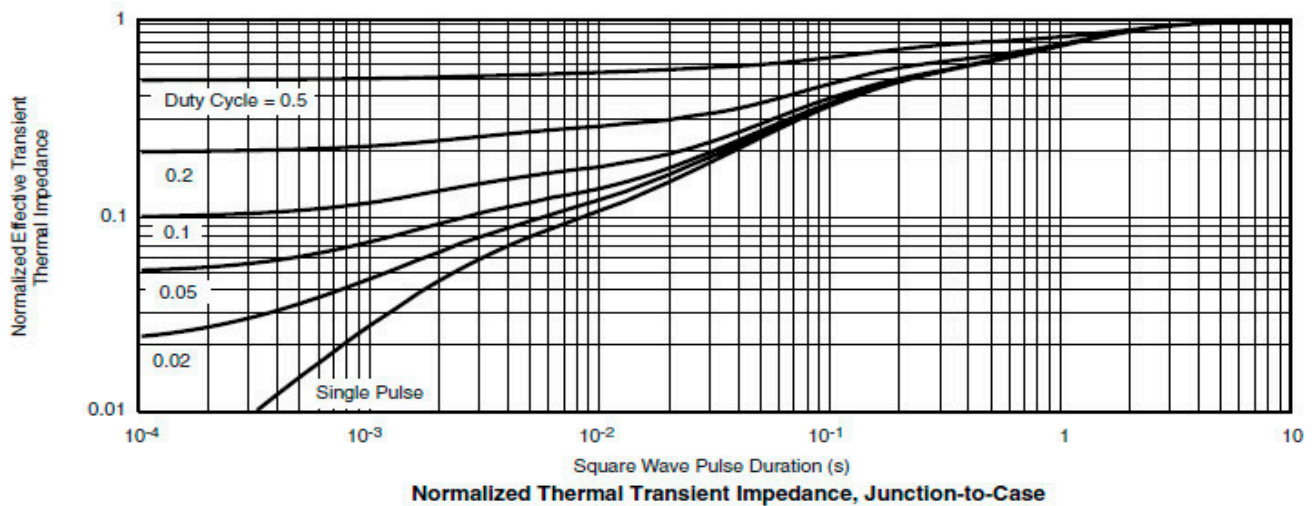
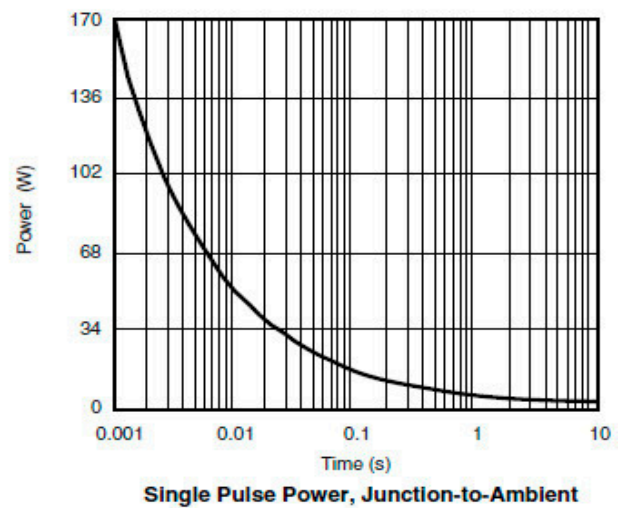
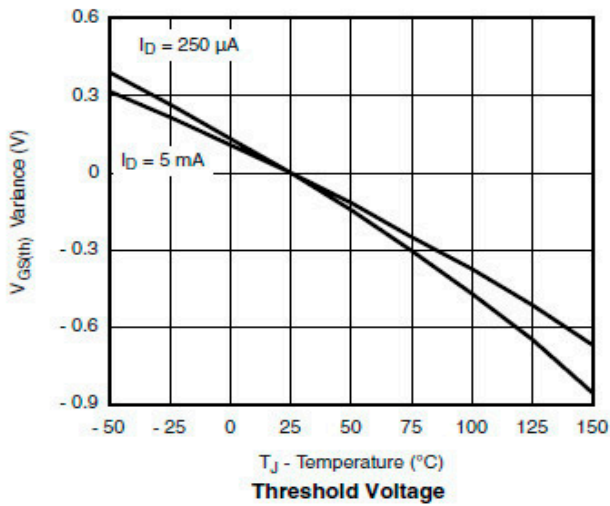
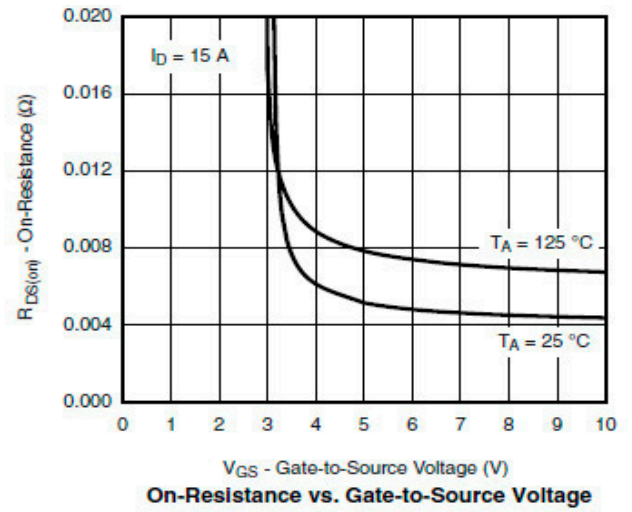
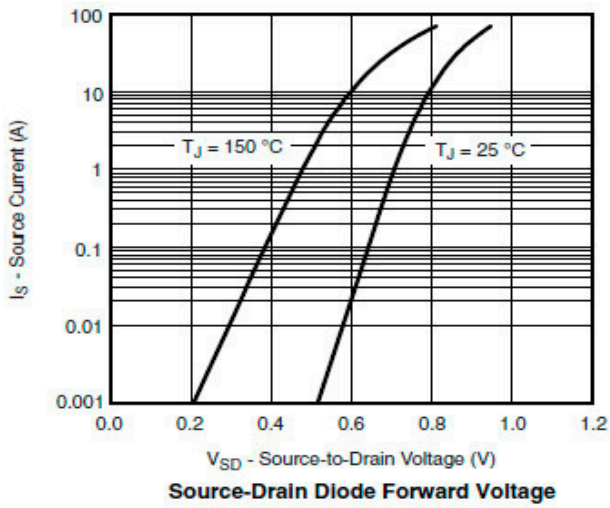
Gate Charge



On-Resistance vs. Junction Temperature

Single N-channel MOSFET

ELM544634A-N

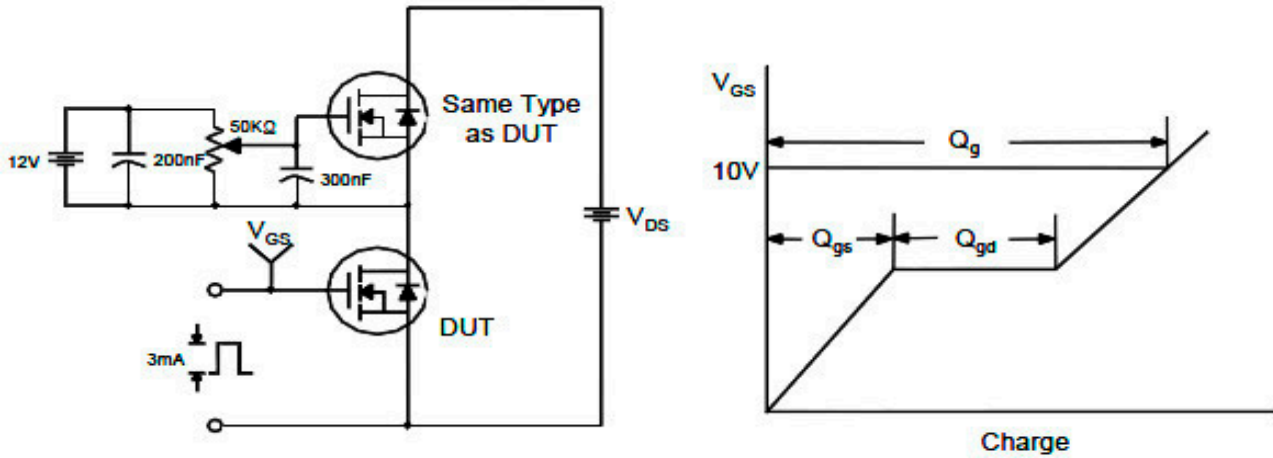


Single N-channel MOSFET

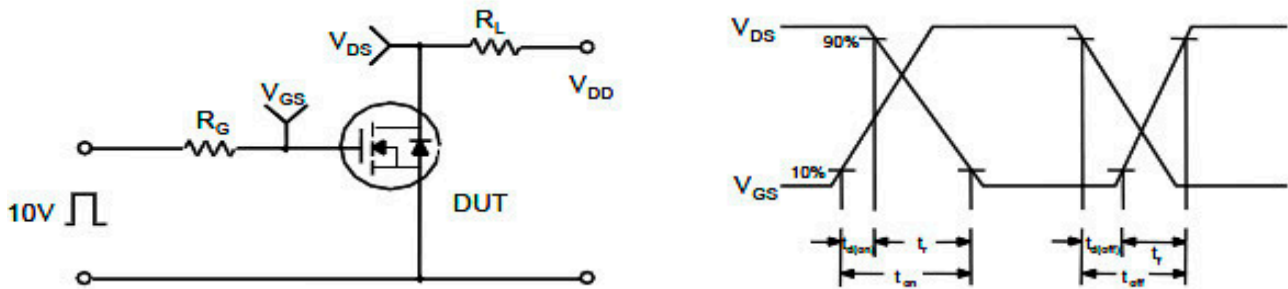
ELM544634A-N

■ Test circuit and waveform

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

